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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10001314	11/14/2001	438	-112	2812	<i>[Signature]</i>

**APPLICANTS: Kirn Chang; Kim Wan;

**CONTINUING DATA VERIFIED:

** FOREIGN APPLICATIONS VERIFIED:

REPUBLIC OF KOREA 2001-15415 03/24/2001

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	
Foreign priority claimed 35 USC 119 conditions met Verified and Acknowledged Examiners's initials		<input type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> yes <input type="checkbox"/> no	ATTORNEY DOCKET NO TJK/ 204
TITLE : Method for forming isolation layer of semiconductor device			

U S DEPT. OF COMM /PAT & TM-PTO-4361(Rev. 10-94)

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED	
			Total Claims	Print Claim for O.G.
ISSUE FEE		DRAWING		
Amount Due	Date Paid	Sheets Drwg.	Figs.Drwg.	Print Fig.
TERMINAL DISCLAIMER		Primary Examiner		
		PREPARED FOR ISSUE		
		Application Examiner		
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